Journal of Crystal Growth 95 (1989) 625–634
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AUTHOR INDEX

Abstreiter, G., K. Eberl, E. Friess, W. Wegschneider and R. Zachai, Silicon/germanium strained layer superlattices 95 (1989) 431
Ackley, D., see Lee 95 (1989) 292
Adams, P.M., see Chang 95 (1989) 451
Aers, G.C., see Baribeau 95 (1989) 447
Ahearn, J.S., see Uppal 95 (1989) 281
Aizaka, N., see Hirayama 95 (1989) 476
Akatsuka, T., see Yamada 95 (1989) 145
Akiba, S., see Hashimoto 95 (1989) 599
Alaoui, F., see Benchimol 95 (1989) 150
Alexandre, F., see Benchimol 95 (1989) 150
Alves, E.S., see Hughes 95 (1989) 352
Anan, T., see Nishi 95 (1989) 202
Andersson, T.G., Z.-G. Chen, Z.-Y. Xu, J.-Z. Xu and W.-K. Ge, Hot carrier photoluminescence from strained $In_xGa_{1-x}As$/GaAs single quantum wells 95 (1989) 215
Ando, M., see Koshiba 95 (1989) 51
Andrews, D.A., M.A.Z. Rejman-Greene, B. Wakefield and G.J. Davies, Selective area growth of indium phosphide based heterostructures by metalorganic molecular beam epitaxy 95 (1989) 167
Aoyagi, Y., see Nagata 95 (1989) 142
Arrott, A.S., see Petrich 95 (1989) 23
Artique, C., see Goldstein 95 (1989) 375
Asahi, H., see Kaneko 95 (1989) 158
Asano, T., see Tsutsui 95 (1989) 398
Ashenford, D.E., B. Lunn, J.J. Davies, J.H.C. Hogg, J.E. Nicholls, C.G. Scott, D. Shaw, H.H. Sutherland, C.P. Hilton, T.J. Gregory and D. Johnston, MBE growth of CdTe and $Cd_{1-x}Mn_xTe$ layers and multilayers on InSb substrates 95 (1989) 557
Ashley, T., see McConville 95 (1989) 228
Asonen, H., see Lilja 95 (1989) 522
Auvray, P., M. Baudet and A. Regreny, X-ray diffraction effects in Ga and Al arsenide structures MBE-grown on slightly misoriented GaAs (001) substrates 95 (1989) 288

Balk, P., see Kamp 95 (1989) 154
Ballini, Y., see Guivarc'h 95 (1989) 427
Bando, Y., see Iijima 95 (1989) 505
Bando, Y., see Terashima 95 (1989) 617
Baribeau, J.-M., D.C. Houghton, D.J. Lockwood, M.W.C. Dharma-Wardana and G.C. Aers, Epitaxy of Si–Ge heterostructures by Si MBE 95 (1989) 447
Barthe, F., see Houzay 95 (1989) 35
Batra, S., see Pukite 95 (1989) 269
Battersby, S.J., see Harris 95 (1989) 257
Baudet, M., see Auvray 95 (1989) 288
Baukus, J.P., see Wu 95 (1989) 594
Beall, R.B., see Harris 95 (1989) 257
Beeby, J.L., Simulation of MBE growth 95 (1989) 48
Beggy, J.C., see Tu 95 (1989) 140
Benchimol, J.L., F. Alexandre, Y. Gao and F. Alaoui, Growth parameter dependence of background doping level in GaAs, $In_{0.53}Ga_{0.47}As$ and $Al_xGa_{1-x}As$ grown by metalorganic molecular beam epitaxy 95 (1989) 150
Benoit, J., see Goldstein 95 (1989) 375
Benson, J.D., D. Rajavel, B.K. Wagner, R. Benz II and C.J. Summers, Properties of undoped and Sb-doped CdTe surfaces prepared by conventional and photo-assisted molecular beam epitaxy 95 (1989) 543
Benz II, R., see Benson 95 (1989) 543
Berger, P., see Pamulapati 95 (1989) 193
Bhattacharya, P., see Pamulapati 95 (1989) 193
Bimberg, D., see Meier 95 (1989) 66
Blunier, S., see Zogg 95 (1989) 562
Bonnevie, D., see Goldstein 95 (1989) 375
Bowman, Jr., R.C., see Chang 95 (1989) 451
Brown, G.T., see McConville 95 (1989) 228

Casel, A., see Jorke 95 (1989) 484
Caulet, J., see Guivarc'h 95 (1989) 427
Celeste, A., see Hughes 95 (1989) 352
Chan, W.K., see Harbison 95 (1989) 425
Chang, A.M., see Cunningham 95 (1989) 253
Chang, K., see Pamulapati 95 (1989) 193
Chang, L.L., see Munekata 95 (1989) 235
Chang, S.J., C.F. Huang, M.A. Kallel, K.L. Wang, R.C. Bowman, Jr. and P.M. Adams, Study of ultra-thin Ge/Si strained layer superlattice 95 (1989) 451
Chazelas, J., see Etienne 95 (1989) 410
Chen, Y., see Pamulapati 95 (1989) 193
Chen, Z.-G., see Andersson 95 (1989) 215
Cheng, H., J.M. DePuydt, J.E. Potts and M.A. Haase, Growth of p- and n-type ZnSe by molecular beam epitaxy 95 (1989) 512
Chiu, T.H., J.E. Cunningham and A. Robertson, Jr., Surface chemical kinetics during the growth of GaAs by chemical beam epitaxy 95 (1989) 136
Chiu, T.H., see Cunningham 95 (1989) 185
Chiu, T.H., see Cunningham 95 (1989) 253

Chiu, T.H., see Cunningham 95 (1989) 253
Cho, A.Y., Current state and future challenge in molecular beam epitaxy (MBE) research 95 (1989) 1
Clarke, S., D.D. Vvedensky and M.W. Ricketts, Influence of surface morphology upon recovery kinetics during interrupted epitaxial growth 95 (1989) 28
Claxton, P.A., see Hashimoto 95 (1989) 403
Clegg, J.B., see Harris 95 (1989) 257
Cohen, P.I., see Petrich 95 (1989) 23
Cohen, P.I., see Pukite 95 (1989) 269
Coldren, L., see Petroff 95 (1989) 260
Colvard, C., see Lee 95 (1989) 292
Contini, R., see Kamp 95 (1989) 154
Cooper, Jr., J.A., see Qian 95 (1989) 567
Copel, M.W., see Iyer 95 (1989) 439
Courtney, S.J., see McConville 95 (1989) 228
Creuzet, G., see Etienne 95 (1989) 410
Cullis, A.G., see McConville 95 (1989) 228
Cunningham, J.E., see Chiu 95 (1989) 136
Cunningham, J.E., G. Timp, T.H. Chiu, J.A. Ditzenberger, W.T. Tsang, A.M. Sergent and D.V. Lang, Very high purity GaAs grown by gas source molecular beam epitaxy 95 (1989) 185
Cunningham, J.E., G. Timp, A.M. Chang, T.H. Chiu, W. Jan, E.F. Schubert and W.T. Tsang, Spatial localization of Si in selectively δ-doped $Al_xGa_{1-x}As/GaAs$ heterostructures for high mobility and density realization 95 (1989) 253

Dal'bo, F., see Magnea 95 (1989) 584
Davies, G.J., see Andrews 95 (1989) 167
Davies, J.J., see Ashenford 95 (1989) 557
Den, S., see Nagata 95 (1989) 142
Denhoff, M.W., see Teo 95 (1989) 486
DePuydt, J.M., see Cheng 95 (1989) 512
Dharma-Wardana, M.W.C., see Baribeau 95 (1989) 447
Di Cioccio, L., A. Million, J. Piaguet, G. Rolland, G. Lentz, N. Magnea and H. Mariette, Twin free growth of II–VI compounds on (111) CdZnTe substrates by molecular beam epitaxy 95 (1989) 552
Ditzenberger, J.A., see Cunningham 95 (1989) 185
Doi, T. and M. Ichikawa, Microscopic observation of Si MBE on Si(001) surface using microprobe RHEED 95 (1989) 468
Donnelly, V.M., see Tu 95 (1989) 140
Dosho, S., Y. Takemura, M. Konagai and K. Takahashi, Atomic layer epitaxy of ZnSe–ZnTe strained layer superlattices 95 (1989) 580
Duggan, G., see Harris 95 (1989) 257

Eaves, L., see Hughes 95 (1989) 352
Eberl, K., see Abstreiter 95 (1989) 431
Eckstein, J.N., see Harris 95 (1989) 607
English, J.H., see Gossard 95 (1989) 247
English, J.H., see Petroff 95 (1989) 260
Epperlein, P.W., see Meier 95 (1989) 66
Esaki, L., see Hong 95 (1989) 266
Etienne, P., J. Chazelas, G. Creuzet, A. Friederich, J. Massies, F. Nguyen-Van-Dau and A. Fert, Growth of single-crystal Fe/Cr magnetic multilayer structures on (001) GaAs by molecular beam epitaxy 95 (1989) 410
Evans, K.R., C.E. Stutz, D.K. Lorance and R.L. Jones, Effects of strain and surface reconstruction on the kinetics of indium incorporation in MBE growth of InAs 95 (1989) 197

Fang, Z.-Q., see Li 95 (1989) 296
Fasol, G., M. Tanaka, H. Sakaki and Y. Horikoshi, Interface roughness and confined LO phonons in quantum wells 95 (1989) 75
Fernier, B., see Goldstein 95 (1989) 375
Fert, A., see Etienne 95 (1989) 410
Feuillet, G., see Magnea 95 (1989) 584
Florez, L.T., see Harbison 95 (1989) 425
Forchel, A., see Leier 95 (1989) 277
Foxon, C.T., Current understanding of growth mechanisms in III–V MBE 95 (1989) 11
Foxon, C.T., see Harris 95 (1989) 257
Franklin, J., see Pao 95 (1989) 301
Friederich, A., see Etienne 95 (1989) 410
Friess, E., see Abstreiter 95 (1989) 431
Fujii, T., see Ueda 95 (1989) 38
Fujii, T., see Sasa 95 (1989) 189
Fujii, T., see Sugiyama 95 (1989) 363
Fujii, T., see Wada 95 (1989) 378
Fujita, Sz., Y. Nakaoka, T. Uemura, M. Tabuchi, S. Noda, Y. Takeda and A. Sasaki, RHEED and X-ray characterization of InGaAs/GaAs grown by MBE 95 (1989) 224
Fujiwara, K., see Kanamoto 95 (1989) 273
Furukawa, S., see Tsutsui 95 (1989) 398
Fuyuki, T., M. Nakayama, T. Yoshinobu, H. Shiomi and H. Matsunami, Atomic layer epitaxy of cubic SiC by gas source MBE using surface superstructure 95 (1989) 461

Gaines, J., see Petroff 95 (1989) 260
Gao, Y., see Benchimol 95 (1989) 150
Ge, W.-K., see Andersson 95 (1989) 215
Gibala, R., see Pamulapati 95 (1989) 193
Gibson, W.M., see Hashimoto 95 (1989) 403
Glenn, J.L., see Qian 95 (1989) 567
Goldman, V.J., see Shayegan 95 (1989) 250
Goldstein, L., C. Artique, D. Bonnevie, B. Fernier, A. Perales and J. Benoit, Distributed feedback (DFB) lasers at 1.5 μm grown by gas source molecular beam epitaxy (GSMBE) 95 (1989) 375

Gonda, S., see Kaneko 95 (1989) 158
Gossard, A.C., J.H. English, M. Miller and R.J. Simes, Growth and doping of heterostructures for high electron mobilities 95 (1989) 247
Gossard, A.C., see Petroff 95 (1989) 260
Gotoda, M., see Morishita 95 (1989) 176
Gotoh, H., see Nagao 95 (1989) 163
Gregory, T.J., see Ashenford 95 (1989) 557
Guenais, B., see Guivarc'h 95 (1989) 427
Guérin, R., see Guivarc'h 95 (1989) 427
Guille, C., see Houzay 95 (1989) 35
Guivarc'h, A., J. Caulet, B. Guenais, Y. Ballini, R. Guérin, A. Poudoulec and A. Regreny, Growth of Ni_3Ga_2, NiGa and Ni_2Ga_3 on GaAs (001) and (111) in a molecular beam epitaxy system 95 (1989) 427
Gunshor, R.L., see Venkatasubramanian 95 (1989) 533
Gunshor, R.L., see Qian 95 (1989) 567
Gunshor, R.L., see Nurmikko 95 (1989) 589

Haase, M.A., see Cheng 95 (1989) 512
Haggerott, M., see Qian 95 (1989) 567
Hagino, M., see Zhu 95 (1989) 529
Hamaguchi, H., see Wada 95 (1989) 378
Hanafusa, H., see Ogata 95 (1989) 500
Harbison, J.P., T. Sands, N. Tabatabaie, W.K. Chan, L.T. Florez and V.G. Keramidas, MBE growth of AlGaAs/NiAl/AlGaAs heterostructures: a novel epitaxial III–V semiconductor/metal system 95 (1989) 425
Harder, C., see Meier 95 (1989) 66
Harris, J.J., R.B. Beall, J.B. Clegg, C.T. Foxon, S.J. Battersby, D.E. Lacklison, G. Duggan and C.M. Hellon, Si migration effects in GaAs/(Al,Ga)As heterojunction and δ-doped structures 95 (1989) 257
Harris, J.S., see Pao 95 (1989) 301
Harris, J.S., see Pao 95 (1989) 305
Harris, J.S., J.N. Eckstein, E.S. Hellmann and D.G. Schlomm, MBE growth of high critical temperature superconductors 95 (1989) 607
Hasegawa, H., see Ishii 95 (1989) 132
Hasegawa, H., see Ohno 95 (1989) 367
Hasegawa, S., K. Maehashi, H. Nakashima, T. Ito and A. Hiraki, Growth and characterization of GaAs films on porous Si 95 (1989) 113
Hashimoto, M., see Tanaka 95 (1989) 386
Hashimoto, S., W.M. Gibson, L.J. Schowalter, E.Y. Lee and P.A. Claxton, Reduction of strain in GaAs grown on CaF_2/Si heteroepitaxial substrates 95 (1989) 403
Hashimoto, S., N. Koguchi, S. Takahashi and S. Akiba, Molecular beam epitaxial growth and photoluminescence of PbS–PbCdSSe single quantum wells 95 (1989) 599
Hayakawa, T., see Takahashi 95 (1989) 333
Hayakawa, T., K. Takahashi, K. Sasaki, S. Yamamoto and T. Hijikata, Molecular beam epitaxial growth of $(Al_yGa_{1-y})_x In_{1-x}P$ ($x \sim 0.5$) on (100) GaAs 95 (1989) 343
Hayashi, K., see Sonoda 95 (1989) 317
Hayashi, Y., see Kawanami 95 (1989) 117
Heinecke, H., see Kamp 95 (1989) 154
Hellmann, E.S., see Harris 95 (1989) 607
Hellon, C.M., see Harris 95 (1989) 257
Henini, M., see Hughes 95 (1989) 352
Herman, M.A., Near surface transition layer model of MBE growth 95 (1989) 64
Herring, R., see Uppal 95 (1989) 281
Herzog, H.-J., see Jorke 95 (1989) 484
Heyen, T., see Qian 95 (1989) 567
Hijikata, T., see Takahashi 95 (1989) 333
Hijikata, T., see Hayakawa 95 (1989) 343
Hill, G., see Hughes 95 (1989) 352
Hilton, C.P., see Ashenford 95 (1989) 557
Hiraki, A., see Hasegawa 95 (1989) 113
Hirama, K., see Sakai 95 (1989) 621
Hirata, K., see Terashima 95 (1989) 617
Hirayama, H., T. Tatsumi and N. Aizaka, Disilane gas source Si-MBE 95 (1989) 476
Hirotsu, Y., see Otsuka 95 (1989) 43
Hishida, Y., H. Ishii, T. Toda and T. Niina, Growth and characterization of MBE-grown ZnTe:P 95 (1989) 517
Hobson, G.I., B. Khamsehpour, K.E. Singer and W.S. Truscott, MBE growth of pseudomorphic $GaAs_ySb_{1-y}$ in a GaAs host lattice 95 (1989) 220
Hogg, J.H.C., see Ashenford 95 (1989) 557
Hong, J.M., T.P. Smith III, K.Y. Lee, C.M. Knoedler, S.E. Laux, D.P. Kern and L. Esaki, One- and zero-dimensional systems: fabrication and characterization 95 (1989) 266
Horikoshi, Y. and M. Kawashima, Migration-enhanced epitaxy of GaAs and AlGaAs 95 (1989) 17
Horikoshi, Y., see Fasol 95 (1989) 75
Horikoshi, Y., see Stolz 95 (1989) 87
Hosoda, M., see Takahashi 95 (1989) 333
Houghton, D.C., see Baribeau 95 (1989) 447
Houzay, F., J.M. Moison, C. Guille, F. Barthe and M. Van Rompay, Surface segregation of third-column atoms in III–V ternary arsenides 95 (1989) 35
Huang, C.F., see Chang 95 (1989) 451
Hughes, O.H., M. Henini, E.S. Alves, L. Eaves, M.L. Leadbeater, F.W. Sheard, G. Hill, M.A. Pate, J.C. Portal and A. Celeste, Investigation of asymmetric double barrier resonant tunneling structures based on (AlGa)As/GaAs 95 (1989) 352

Ichikawa, M., see Doi 95 (1989) 468
Ichimiya, A., see Nakahara 95 (1989) 472
Ichimori, T., M. Tabe and Y. Sakakibara, Preparation and characterization of SiN_x

films epitaxially grown on Si(111) substrates 95 (1989) 464
Ide, Y., see Nishi 95 (1989) 202
Igarashi, I., see Tanaka 95 (1989) 386
Igarashi, T., see Kondo 95 (1989) 309
Ihm, Y.E., see Otsuka 95 (1989) 43
Iijima, K., T. Terashima, K. Yamamoto and Y. Bando, Formation and structures of NiO–ZnO artificial superlattices 95 (1989) 505
Iijima, K., see Terashima 95 (1989) 617
Iimura, Y., see Nagata 95 (1989) 142
Imamoto, H., see Sato 95 (1989) 206
Imanaka, K., see Sato 95 (1989) 206
Inata, T., S. Muto, S. Sasa and E. Miyauchi, Determination of the resonant-state energy of an $In_{0.53}Ga_{0.47}As/AlAs$ pseudomorphic resonant tunneling barrier grown by MBE 95 (1989) 371
Inoue, K., see Matsuno 95 (1989) 390
Inoue, Y., see Nagao 95 (1989) 163
Ishida, M., see Sawada 95 (1989) 494
Ishida, T., see Sakai 95 (1989) 621
Ishii, H., H. Ohno, K. Matsuzaki and H. Hasegawa, Effect of exposure to group III alkyls on compound semiconductor surfaces observed by X-ray photoelectron spectroscopy 95 (1989) 132
Ishii, H., see Ohno 95 (1989) 367
Ishii, H., see Hishida 95 (1989) 517
Ishii, M., see Kanamoto 95 (1989) 273
Ishikawa, T., see Kondo 95 (1989) 309
Ishikawa, T., see Saito 95 (1989) 322
Ishiwara, H., see Tsutsui 95 (1989) 398
Ito, H., see Shayegan 95 (1989) 250
Ito, M., see Sonoda 95 (1989) 317
Ito, T., see Hasegawa 95 (1989) 113
Iyer, S.S., P.R. Pukite, J.C. Tsang and M.W. Copel, Growth of abrupt Ge layers in Si(100) 95 (1989) 439

Jagannath, C., see Yacobi 95 (1989) 240
Jan, W., see Cunningham 95 (1989) 253
Jeong, J.C., see Li 95 (1989) 296
Jiang, C., see Shayegan 95 (1989) 250
Johnston, D., see Ashenford 95 (1989) 557
Jones, R.L., see Evans 95 (1989) 197
Jorke, H., H. Kibbel, F. Schäffler, A. Casel, H.-J. Herzog and E. Kasper, Very low temperature growth and doping of silicon MBE layers 95 (1989) 484

Kallel, M.A., see Chang 95 (1989) 451
Kamath, G.S., see Wu 95 (1989) 594
Kamp, M., R. Contini, K. Werner, H. Heinecke, M. Weyers, H. Lüth and P. Balk, Carbon incorporation in MOMBE-grown $Ga_{0.47}In_{0.53}As$ 95 (1989) 154
Kan, Y., see Kunitsugu 95 (1989) 91
Kanamoto, K., K. Fujiwara, Y. Tokuda, N. Tsukada, M. Ishii and T. Nakayama, Surface diffusion during MBE growth of GaAs–AlGaAs single quantum wells on vicinal surfaces 95 (1989) 273
Kanaya, Y., see Tsuji 95 (1989) 405
Kaneko, T., H. Asahi, Y. Okuno and S. Gonda, MOMBE (metalorganic molecular beam epitaxy) growth of InGaSb on GaSb 95 (1989) 158
Kano, H., see Tanaka 95 (1989) 386
Karasawa, T., K. Ohkawa and T. Mitsuyu, MBE-grown ZnTe–ZnS strained-layer superlattices 95 (1989) 547
Kasai, H., see Yoshikawa 95 (1989) 572
Kasai, J., see Mishima 95 (1989) 338
Kasper, E., see Jorke 95 (1989) 484
Kato, H., see Matsushima 95 (1989) 210
Kato, K., see Sakai 95 (1989) 621
Katoh, M., see Nagao 95 (1989) 163
Kawabe, M., see Yokoyama 95 (1989) 32
Kawabe, M. and T. Shiraishi, Initial stage of epitaxy of GaAs on Si 95 (1989) 103
Kawaguchi, Y. and K. Nakashima, Sn doping for InP and InGaAs grown by metalorganic molecular beam epitaxy using tetraethyltin 95 (1989) 181
Kawamura, Y., K. Wakita and O. Mikami, High on/off ratio bistable operation of InGaAs/InAlAs MQW lasers using resonant tunneling effect 95 (1989) 349
Kawanaka, M. and J. Sone, Doping properties of Ge on GaAs (100) grown by MBE 95 (1989) 421
Kawanami, H., see Yao 95 (1989) 107
Kawanami, H. and Y. Hayashi, Molecular beam epitaxy of single domain InP films directly grown on Si(001) substrates 95 (1989) 117
Kawashima, M., see Horikoshi 95 (1989) 17
Kawata, H., see Koshiba 95 (1989) 51
Keramidas, V.G., see Harbison 95 (1989) 425
Kern, D.P., see Hong 95 (1989) 266
Keskinen, J., see Lilja 95 (1989) 522
Khamsehpour, B., see Hobson 95 (1989) 220
Kibbel, H., see Jorke 95 (1989) 484
Kim, H.K., see Li 95 (1989) 296
Kimata, M., see Satoh 95 (1989) 564
Kitagawa, M., Y. Tomomura, A. Suziki and S. Nakajima, Homoepitaxial growth of low-resistivity-Al-doped ZnS single crystal films by molecular beam epitaxy 95 (1989) 509
Klem, J., see Otsuka 95 (1989) 43
Knoedler, C.M., see Hong 95 (1989) 266
Kobayashi, M., see Qian 95 (1989) 567
Kobiki, M., see Sonoda 95 (1989) 317
Koguchi, N., see Hashimoto 95 (1989) 599
Kojima, T., see Ohta 95 (1989) 71

Kojima, T., see Nakagawa 95 (1989) 357
Kolodziejski, L.A., see Venkatasubramanian 95 (1989) 533
Kolodziejski, L.A., see Qian 95 (1989) 567
Kolodziejski, L.A., see Nurmikko 95 (1989) 589
Koma, A., see Saiki 95 (1989) 603
Konagai, M., see Yamada 95 (1989) 145
Konagai, M., see Dosho 95 (1989) 580
Kondo, K., J. Saito, T. Igarashi, K. Nanbu and T. Ishikawa, MBE as a production technology for HEMT LSIs 95 (1989) 309
Kondo, K., see Saito 95 (1989) 322
Koshiba, S., S. Nanao, O. Tsuda, Y. Watanabe, Y. Sakurai, K. Sakaki, H. Kawata and M. Ando, Effects of growth interruption on structure of MBE grown GaAs/AlAs hetero-interfaces studied by X-ray diffraction 95 (1989) 51
Krahl, M., see Meier 95 (1989) 66
Kroemer, H., T.Y. Liu and P.M. Petroff, GaAs on Si and related systems: problems and prospects 95 (1989) 96
Kroemer, H., see Petroff 95 (1989) 260
Kukimoto, H., MOCVD – current state and future 95 (1989) 360
Kunitsugu, Y., I. Suemune, Y. Tanaka, Y. Kan and M. Yamanishi, Low-temperature cleaning of Si and growth of GaAs on Si by hydrogen plasma-assisted metalorganic molecular-beam epitaxy 95 (1989) 91

Lacklison, D.E., see Harris 95 (1989) 257
Landheer, D., see Teo 95 (1989) 486
Lang, D.V., see Cunningham 95 (1989) 185
Laux, S.E., see Hong 95 (1989) 266
Leadbeater, M.L., see Hughes 95 (1989) 352
Lee, E.Y., see Hashimoto 95 (1989) 403
Lee, H., N. Nouri, C. Colvard and D. Ackley, Comparison of RHEED during MBE growth and the quality of AlGaAs:Si grown on (100) and misoriented GaAs substrates 95 (1989) 292
Lee, K.Y., see Hong 95 (1989) 266
Leier, H., H. Rothfritz, A. Forchel and G. Weimann, Optical properties of thermally interdiffused MBE-grown GaAs/GaAlAs quantum wells 95 (1989) 277
Lentz, G., see Di Cioccio 95 (1989) 552
Lentz, G., see Magnea 95 (1989) 584
Li, Aizhen, H.K. Kim, J.C. Jeong, D. Wong, J.H. Zhao, Z.-Q. Fang, T.E. Schlesinger and A.G. Milnes, Trap gettering by isoelectronic doping of p-GaAs and n-GaAs grown by molecular beam epitaxy 95 (1989) 296
Lilja, J., J. Keskinen, H. Asonen and M. Pessa, Growth of ZnSe films on GaAs ⟨100⟩ substrates by conventional and pulsed molecular beam epitaxy 95 (1989) 522
Liu, D., see Pao 95 (1989) 305
Liu, T.Y., see Kroemer 95 (1989) 96
Lockwood, D.J., see Baribeau 95 (1989) 447
Lorance, D.K., see Evans 95 (1989) 197
Lunn, B., see Ashenford 95 (1989) 557
Lüth, H., see Kamp 95 (1989) 154

Maehashi, K., see Hasegawa 95 (1989) 113
Magnea, N., see Di Cioccio 95 (1989) 552
Magnea, N., G. Lentz, H. Mariette, G. Feuillet, F. Dal'bo and H. Tuffigo, Growth and characterization of CdTe single quantum wells confined by $Cd_{1-x}Zn_xTe$ alloy and short period CdTe/ZnTe superlattice 95 (1989) 584
Maissen, C., see Zogg 95 (1989) 562
Makiuchi, M., see Wada 95 (1989) 378
Mariette, H., see Di Cioccio 95 (1989) 552
Mariette, H., see Magnea 95 (1989) 584
Marks, R.F., see Wright 95 (1989) 245
Marshall, E.D., see Wright 95 (1989) 245
Maruno, S., see Morishita 95 (1989) 176
Masek, J., see Zogg 95 (1989) 562
Massies, J., see Turco 95 (1989) 201
Massies, J., see Etienne 95 (1989) 410
Matsumura, N., M. Tsubokura and J. Saraie, Lattice strain and its effects on energy band structure in MBE-$ZnSe_xSe_{1-x}$/GaAs 95 (1989) 525
Matsunami, H., see Ozasa 95 (1989) 171
Matsunami, H., see Fuyuki 95 (1989) 461
Matsuno, T., K. Nishii and K. Inoue, Growth and properties of N-AlGaAs/InGaAs selectively-doped single- and double-heterojunction FET structures 95 (1989) 390
Matsushima, Y., H. Kato, K. Utaka and K. Sakai, MBE growth of InAs/AlInAs strained-layer multi quantum wells for optical device applications 95 (1989) 210
Matsuzaki, K., see Ishii 95 (1989) 132
Matsuzaki, K., see Ohno 95 (1989) 367
Mazaki, H., see Terashima 95 (1989) 617
Mbaye, A.A., see Turco 95 (1989) 201
McCaulley, J.A., see Tu 95 (1989) 140
McConfille, C.F., C.R. Whitehouse, G.M. Williams, A.G. Cullis, T. Ashley, M.S. Skolnick, G.T. Brown and S.J. Courtney, Interfacial studies and electrical characterisation of heteroepitaxial InSb on GaAs (100) grown by MBE 95 (1989) 228
McCrary, V.R., see Tu 95 (1989) 140
McMullin, J.N., see Teo 95 (1989) 486
Meier, H.P., E. Van Gieson, P.W. Epperlein, C. Harder, W. Walter, M. Krahl and D. Bimberg, Surface diffusion effects in MBE growth of QWs on channeled substrate (100) GaAs for lasers 95 (1989) 66
Melloch, M.R., see Qian 95 (1989) 567

Mikami, O., see Kawamura 95 (1989) 349
Miki, K., K. Sakamoto, T. Sakamoto, H. Okumura, N. Takahashi and S. Yoshida, Ge_m/Si_m strained-layer superlattices fabricated by phase-locked epitaxy 95 (1989) 444
Miller, M., see Gossard 95 (1989) 247
Million, A., see Di Cioccio 95 (1989) 552
Milnes, A.G., see Li 95 (1989) 296
Mishima, T., J. Kasai, Y. Uchida and S. Takahashi, Optical properties of high-quality InAlAs/InGaAs SQWs grown by MBE using specially refined In and Al sources 95 (1989) 338
Mishima, T., T. Tanoue and K. Uomi, Low temperature MBE growth of high quality modulation doped AlGaAs/GaAs MQWs for ultra-high-speed laser diodes 95 (1989) 382
Mitsui, M., see Sonoda 95 (1989) 317
Mitsuyu, T., see Karasawa 95 (1989) 547
Miyao, M., see Zhu 95 (1989) 529
Miyauchi, E., see Sasa 95 (1989) 189
Miyauchi, E., see Sugiyama 95 (1989) 363
Miyauchi, E., see Inata 95 (1989) 371
Miyauchi, M., see Yamada 95 (1989) 145
Moison, J.M., see Houzay 95 (1989) 35
Morishita, Y., S. Maruno, M. Gotoda, Y. Nomura and H. Ogata, Gas source MBE growth of InP 95 (1989) 176
Morkoç, H., see Otsuka 95 (1989) 43
Morkoç, H., Electronic and optical devices with gallium arsenide on silicon prepared by MBE 95 (1989) 79
Munekata, H., T.P. Smith III and L.L. Chang, Heteroepitaxy of InAs quantum wells 95 (1989) 235
Murakami, S., see Sakai 95 (1989) 621
Muto, S., see Sugiyama 95 (1989) 363
Muto, S., see Inata 95 (1989) 371

Naganuma, M., see Stolz 95 (1989) 87
Nagao, S., Y. Inoue, M. Katoh, K. Shimoyama and H. Gotoh, Growth of (AlIn)P/GaAs single quantum well structure on (001) GaAs by gas source MBE using AsH_3 and PH_3 gas 95 (1989) 163
Nagata, K., Y. Iimura, Y. Aoyagi, S. Namba and S. Den, Photo-assisted chemical beam epitaxy of GaAs 95 (1989) 142
Nakada, Y., see Ueda 95 (1989) 38
Nakagawa, K., see Van Gorkum 95 (1989) 480
Nakagawa, K., see Ohshima 95 (1989) 490
Nakagawa, T., see Ohta 95 (1989) 71
Nakagawa, T., T. Kojima and K. Ohta, Tunneling of X-point electrons in triple barrier diodes 95 (1989) 357
Nakahara, H. and A. Ichimiya, RHEED intensity rocking curves from Si(111) surface during MBE growth 95 (1989) 472
Nakajima, S., see Kitagawa 95 (1989) 509
Nakamura, N., see Ohshima 95 (1989) 490
Nakamura, T., see Sawada 95 (1989) 494
Nakao, H., see Yao 95 (1989) 107
Nakaoka, Y., see Fujita 95 (1989) 224
Nakashima, H., see Hasegawa 95 (1989) 113
Nakashima, K., see Kawaguchi 95 (1989) 181
Nakata, Y., see Sasa 95 (1989) 189
Nakata, Y., see Sugiyama 95 (1989) 363
Nakayama, M., see Fuyuki 95 (1989) 461
Nakayama, T., see Kanamoto 95 (1989) 273
Namba, S., see Nagata 95 (1989) 142
Nanao, S., see Koshiba 95 (1989) 51
Nanbu, K., see Kondo 95 (1989) 309
Nanbu, K., see Saito 95 (1989) 322
Nguyen-Van-Dau, F., see Etienne 95 (1989) 410
Nicholls, J.E., see Ashenford 95 (1989) 557
Niina, T., see Hishida 95 (1989) 517
Nishi, K., T. Anan, Y. Ide and K. Onabe, Structural and optical studies on molecular beam epitaxially grown $(InAs)_m$ $(AlAs)_m$ and $(InAs)_m(GaAs)_m$ short-period strained layer superlattices 95 (1989) 202
Nishii, K., see Matsuno 95 (1989) 390
Nobuhara, H., see Wada 95 (1989) 378
Noda, S., see Fujita 95 (1989) 224
Noda, T., M. Tanaka and H. Sakaki, Electron mobility and roughness scattering in potential inserted quantum wells (PI-QWs) 95 (1989) 60
Nomura, T., see Zhu 95 (1989) 529
Nomura, Y., see Morishita 95 (1989) 176
Nouri, N., see Lee 95 (1989) 292
Nozawa, K., see Stolz 95 (1989) 87
Nurmikko, A.V., see Qian 95 (1989) 567
Nurmikko, A.V., L.A. Kolodziejski and R.L. Gunshor, Physics and engineering of diluted magnetic semiconductor superlattices 95 (1989) 589

O, Sungki, see Qian 95 (1989) 567
Ogata, H., see Morishita 95 (1989) 176
Ogata, H., H. Hanafusa and K. Yoneda, Development of a new MBE growth method for fabrication of high quality, double epitaxial $Si/\gamma\text{-}Al_2O_3/Si$ structures 95 (1989) 500
Oh, J., see Pamulapati 95 (1989) 193
Ohishi, M., H. Saito, H. Okano and K. Ohmori, Photo-assisted MBE growth of ZnSe crystals 95 (1989) 538
Ohkawa, K., see Karasawa 95 (1989) 547
Ohmori, K., see Ohishi 95 (1989) 538
Ohno, H., see Ishii 95 (1989) 132
Ohno, H., H. Ishii, K. Matsuzaki and H. Hasegawa, Absence of growth sequence dependence of AlAs/GaAs heterojunction band discontinuity determined by X-ray photoelectron spectroscopy 95 (1989) 367

Ohshima, T., K. Nakagawa, N. Nakamura and Y. Shiraki, Self-aligned $NiSi_2$ electrode fabrication by MBE and its application to etched-groove permeable base transistor (PBT) 95 (1989) 490
Ohta, K., T. Kojima and T. Nakagawa, Anisotropic surface migration of Ga atoms on GaAs (001) 95 (1989) 71
Ohta, K., see Nakagawa 95 (1989) 357
Ohtsuka, M. and A. Suzuki, Simulation of epitaxial growth over patterned substrates 95 (1989) 55
Okano, H., see Ohishi 95 (1989) 538
Okumura, H., see Miki 95 (1989) 444
Okuno, Y., see Kaneko 95 (1989) 158
Onabe, K., see Nishi 95 (1989) 202
Oniyama, H., see Yoshikawa 95 (1989) 572
Oogi, J., see Yokoyama 95 (1989) 32
Otsuka, N., Y.E. Ihm, Y. Hirotsu, J. Klem and H. Morkoç, Atomic ordering in $GaAs_{0.5}Sb_{0.5}$ grown by molecular beam epitaxy 95 (1989) 43
Otsuka, N., see Venkatasubramanian 95 (1989) 533
Otsuka, N., see Qian 95 (1989) 567
Ozasa, K., M. Yuri, S. Tanaka and H. Matsunami, Growth mechanism of $In_{1-x}Ga_xP$ and $In_{1-x}Al_xP$ in metalorganic molecular beam epitaxy 95 (1989) 171

Pak, K., see Tsuji 95 (1989) 405
Pamulapati, J., P. Berger, K. Chang, J. Oh, Y. Chen, J. Singh, P. Bhattacharya and R. Gibala, Growth phenomena and characteristics of strained $In_xGa_{1-x}As$ on GaAs 95 (1989) 193
Pao, Y.C., J. Franklin and J.S. Harris, Jr., Influence of As_4/Ga flux ratio on Be incorporation in heavily doped GaAs grown by molecular beam epitaxy 95 (1989) 301
Pao, Y.C., D. Liu and J.S. Harris, Jr., Molecular beam epitaxy AlGaAs/GaAs grown in the presence of hydrogen 95 (1989) 305
Pate, M.A., see Hughes 95 (1989) 352
Patten, E.A., see Wu 95 (1989) 594
Perales, A., see Goldstein 95 (1989) 375
Pessa, M., see Lilja 95 (1989) 522
Petrich, G.S., P.R. Pukite, A.M. Wowchak, G.J. Whaley, P.I. Cohen and A.S. Arrott, On the origin of RHEED intensity oscillations 95 (1989) 23
Petrich, G.S., see Pukite 95 (1989) 269
Petroff, P.M., see Kroemer 95 (1989) 96
Petroff, P.M., J. Gaines, M. Tsuchiya, R. Simes, L. Coldren, H. Kroemer, J. English and A.C. Gossard, Band gap modulation in two dimensions by MBE growth of tilted superlattices and applications to quantum confinement structures 95 (1989) 260
Piaguet, J., see Di Cioccio 95 (1989) 552
Portal, J.C., see Hughes 95 (1989) 352
Potts, J.E., see Cheng 95 (1989) 512
Poudoulec, A., see Guivarc'h 95 (1989) 427
Pukite, P.R., see Petrich 95 (1989) 23
Pukite, P.R., G.S. Petrich, S. Batra and P.I. Cohen, The meandering of steps on GaAs(100) 95 (1989) 269
Pukite, P.R., see Iyer 95 (1989) 439

Qian, Q.-D., J. Qiu, J.L. Glenn, Sungki O, R.L. Gunshor, L.A. Kolodziejski, M. Kobayashi, N. Otsuka, M.R. Melloch, J.A. Cooper, Jr., M. Haggerott, T. Heyen and A.V. Nurmikko, II–VI/III–V heterointerfaces: epilayer-on-epilayer structures 95 (1989) 567
Qiu, J., see Venkatasubramanian 95 (1989) 533
Qiu, J., see Qian 95 (1989) 567

Rajavel, D., see Benson 95 (1989) 543
Regreny, A., see Auvray 95 (1989) 288
Regreny, A., see Guivarc'h 95 (1989) 427
Rejman-Greene, M.A.Z., see Andrews 95 (1989) 167
Ricketts, M.W., see Clarke 95 (1989) 28
Robertson, Jr., A., see Chiu 95 (1989) 136
Rolland, G., see Di Cioccio 95 (1989) 552
Rothfritz, H., see Leier 95 (1989) 277

Saiki, K., K. Ueno, T. Shimada and A. Koma, Application of Van der Waals epitaxy to highly heterogeneous systems 95 (1989) 603
Saito, H., see Ohishi 95 (1989) 538
Saito, J., see Kondo 95 (1989) 309
Saito, J., K. Nanbu, T. Ishikawa and K. Kondo, In situ cleaning of GaAs substrates with HCl gas and hydrogen mixture prior to MBE growth 95 (1989) 322
Saito, K., see Yamada 95 (1989) 145
Sajoto, T., see Shayegan 95 (1989) 250
Sakai, J., K. Kato, K. Hirama, S. Murakami and T. Ishida, In situ determination of Ba, Y, Cu and O_2 flux by cold cathode discharge induced emission spectroscopy 95 (1989) 621
Sakai, K., see Matsushima 95 (1989) 210
Sakaki, H., see Koshiba 95 (1989) 51
Sakaki, H., see Noda 95 (1989) 60
Sakaki, H., see Fasol 95 (1989) 75
Sakakibara, Y., see Ichimori 95 (1989) 464
Sakamoto, K., see Miki 95 (1989) 444
Sakamoto, T., see Miki 95 (1989) 444
Sakurai, Y., see Koshiba 95 (1989) 51
Sands, T., see Harbison 95 (1989) 425
Santos, M., see Shayegan 95 (1989) 250
Saraie, J., see Matsumura 95 (1989) 525
Sasa, S., Y. Nakata, Y. Sugiyama, T. Fujii and E. Miyauchi, Electronic properties of two-dimensional electron gas in pseudomorphic $In_xGa_{1-x}As/N - In_{0.52}Al_{0.48}As$ heterostructures 95 (1989) 189

Sasa, S., see Inata 95 (1989) 371
Sasa, S., see Wada 95 (1989) 378
Sasaki, A., see Fujita 95 (1989) 224
Sasaki, K., see Hayakawa 95 (1989) 343
Sato, F., H. Imamoto, K. Imanaka and M. Shimura, High-quality AlGaAs/GaAs quantem well with a short period (InGaAs)(GaAs) strained superlattice buffer layer 95 (1989) 206
Satoh, S. and M. Kimata, Growth of CdTe/α-Sn/CdTe/InSb multilayer structure by MBE 95 (1989) 564
Sawada, K., M. Ishida, T. Nakamura and T. Suzaki, Metalorganic molecular beam epitaxy of γ-Al_2O_3 insulator films on Si with laser irradiation 95 (1989) 494
Schäffler, F., see Jorke 95 (1989) 484
Schlesinger, T.E., see Li 95 (1989) 296
Schlomm, D.G., see Harris 95 (1989) 607
Schmidt-Weinmar, H.G., see Teo 95 (1989) 486
Schowalter, L.J., see Hashimoto 95 (1989) 403
Schrey, F., see Tung 95 (1989) 455
Schubert, E.F., see Cunningham 95 (1989) 253
Schulman, J.N., see Wu 95 (1989) 594
Scott, C.G., see Ashenford 95 (1989) 557
Sergent, A.M., see Cunningham 95 (1989) 185
Shaw, D., see Ashenford 95 (1989) 557
Shayegan, M., V.J. Goldman, T. Sajoto, M. Santos, C. Jiang and H. Ito, MBE growth of two-dimensional electron system with extremely low disorder 95 (1989) 250
Sheard, F.W., see Hughes 95 (1989) 352
Sheldon, P., see Yacobi 95 (1989) 240
Shih, Y.C., see Wright 95 (1989) 245
Shimada, T., see Saiki 95 (1989) 603
Shimoyama, K., see Nagao 95 (1989) 163
Shimura, M., see Sato 95 (1989) 206
Shiomi, H., see Fuyuki 95 (1989) 461
Shiraishi, T., see Kawabe 95 (1989) 103
Shiraki, Y., see Van Gorkum 95 (1989) 480
Shiraki, Y., see Ohshima 95 (1989) 490
Shirland, F.A., see Wu 95 (1989) 594
Simes, R.J., see Gossard 95 (1989) 247
Simes, R.J., see Petroff 95 (1989) 260
Singer, K.E., see Hobson 95 (1989) 220
Singh, J., see Pamulapati 95 (1989) 193
Skolnick, M.S., see McConville 95 (1989) 228
Smith III, T.P., see Munekata 95 (1989) 235
Smith III, T.P., see Hong 95 (1989) 266
Soga, H., see Sugiyama 95 (1989) 394
Sone, J., see Kawanaka 95 (1989) 421
Sonoda, T., M. Ito, M. Kobiki, K. Hayashi, S. Takamiya and M. Mitsui, Ultra-high throughput of GaAs and (AlGa)As layers grown by MBE with a specially designed MBE system 95 (1989) 317
Stolz, W., Y. Horikoshi, M. Naganuma and K. Nozawa, Optimized growth start and controlled formation of misfit dislocations for heteroepitaxial GaAs on (100) Si grown by migration-enhanced epitaxy 95 (1989) 87
Stutz, C.E., see Evans 95 (1989) 197
Suemune, I., see Kunitsugu 95 (1989) 91
Sugiyama, Y., see Sasa 95 (1989) 189
Sugiyama, Y., T. Fujii, Y. Nakata, S. Muto and E. Miyauchi, Conduction-band edge discontinuity of InGaAs/GaAsSb heterostructures lattice-matched to InP grown by molecular beam epitaxy 95 (1989) 363
Sugiyama, Y., H. Soga and M. Tacano, Highly-sensitive Hall element with quantum-well superlattice structures 95 (1989) 394
Summers, C.J., see Benson 95 (1989) 543
Sungki O, see Qian 95 (1989) 567
Sutherland, H.H., see Ashenford 95 (1989) 557
Suzaki, T., see Sawada 95 (1989) 494
Suzuki, A., see Ohtsuka 95 (1989) 55
Suzuki, A., see Kitagawa 95 (1989) 509
Svensson, S.P., see Uppal 95 (1989) 281

Tabatabaie, N., see Harbison 95 (1989) 425
Tabe, M., see Ichimori 95 (1989) 464
Tabuchi, M., see Fujita 95 (1989) 224
Tacano, M., see Sugiyama 95 (1989) 394
Takada, J., see Terashima 95 (1989) 617
Takahashi, K., see Yamada 95 (1989) 145
Takahashi, K., T. Hayakawa, M. Hosoda, S. Yamamoto and T. Hijikata, MBE growth and properties of (100)- and (111)-oriented GaInP/AlInP quantum wells on GaAs substrates 95 (1989) 333
Takahashi, K., see Hayakawa 95 (1989) 343
Takahashi, K., see Dosho 95 (1989) 580
Takahashi, N., see Miki 95 (1989) 444
Takahashi, S., see Mishima 95 (1989) 338
Takahashi, S., see Hashimoto 95 (1989) 599
Takamiya, S., see Sonoda 95 (1989) 317
Takano, Y., see Tsuji 95 (1989) 405
Takeda, Y., see Fujita 95 (1989) 224
Takemura, Y., see Dosho 95 (1989) 580
Tanaka, M., see Noda 95 (1989) 60
Tanaka, M., see Fasol 95 (1989) 75
Tanaka, S., see Ozasa 95 (1989) 171
Tanaka, Y., see Kunitsugu 95 (1989) 91
Tanaka, Y., H. Kano, M. Hashimoto and I. Igarashi, Observation of microwave oscillations (up to 32.6 GHz) from biwell superlattice devices 95 (1989) 386
Tanoue, T., see Mishima 95 (1989) 382
Tatsumi, T., see Hirayama 95 (1989) 476
Teo, K.H., J.N. McMullin, F.L. Weichman, H.G. Schmidt-Weinmar, D. Landheer and M.W. Denhoff, Measurement and mechanism of free carrier recombination in a silicon doping superlattice 95 (1989) 486
Terashima, T., see Iijima 95 (1989) 505

Terashima, T., K. Iijima, K. Yamamoto, J. Takada, K. Hirata, H. Mazaki and Y. Bando, Formation and properties of $YBa_2Cu_3O_{7-x}$ single-crystal thin films by activated reactive evaporation 95 (1989) 617
Timp, G., see Cunningham 95 (1989) 185
Timp, G., see Cunningham 95 (1989) 253
Toba, R., see Yao 95 (1989) 107
Toda, T., see Hishida 95 (1989) 517
Tokuda, Y., see Kanamoto 95 (1989) 273
Tokumitsu, E., see Yamada 95 (1989) 145
Tomomura, Y., see Kitagawa 95 (1989) 509
Torihata, T., see Tsuji 95 (1989) 405
Truscott, W.S., see Hobson 95 (1989) 220
Tsang, J.C., see Iyer 95 (1989) 439
Tsang, W.T., From chemical vapor epitaxy to chemical beam epitaxy 95 (1989) 121
Tsang, W.T., see Cunningham 95 (1989) 185
Tsang, W.T., see Cunningham 95 (1989) 253
Tsubokura, M., see Matsumura 95 (1989) 525
Tsuchiya, M., see Petroff 95 (1989) 260
Tsuda, O., see Koshiba 95 (1989) 51
Tsuji, M., Y. Takano, T. Torihata, Y. Kanaya, K. Pak and H. Yonezu, Molecular beam epitaxial growth of high quality GaAs layer directly on GaP substrate 95 (1989) 405
Tsukada, N., see Kanamoto 95 (1989) 273
Tsutsui, K., T. Asano, H. Ishiwara and S. Furukawa, Growth of single domain GaAs/fluoride/Si structures 95 (1989) 398
Tu, C.W., V.M. Donelly, J.C. Beggy, V.R. McCrary and J.A. McCaulley, Selective-area epitaxy of GaAs by molecular-beam epitaxy (MBE) and metalorganic MBE with excimer laser irradiation 95 (1989) 140
Tuffigo, H., see Magnea 95 (1989) 584
Tung, R.T. and F. Schrey, Growth of single crystal $CoSi_2$ layers at room temperature 95 (1989) 455
Turco, F., A.A. Mbaye and J. Massies, Effects of the elastic strains and relaxations on In-incorporation in (Al,In)As pseudomorphic layers grown by molecular beam epitaxy 95 (1989) 201

Uchida, Y., see Mishima 95 (1989) 338
Ueda, O., T. Fujii, Y. Nakada, H. Yamada and I. Umebu, TEM investigation of modulated structures and ordered structures in InAlAs crystals grown on (001) InP substrates by molecular beam epitaxy 95 (1989) 38
Uemura, T., see Fujita 95 (1989) 224
Ueno, K., see Saiki 95 (1989) 603
Umebu, I., see Ueda 95 (1989) 38
Uomi, K., see Mishima 95 (1989) 382
Uppal, P.N., J.S. Ahearn, S.P. Svensson and R. Herring, Lattice-matched and lattice-mismatched growth on novel GaAs substrate orientations 95 (1989) 281
Utaka, K., see Matsushima 95 (1989) 210

Van Gieson, E., see Meier 95 (1989) 66
Van Gorkum, A.A., K. Nakagawa and Y. Shiraki, Atomic layer doping (ALD) technology in Si and its application to a new structure FET 95 (1989) 480
Van Rompay, M., see Houzay 95 (1989) 35
Venkatasubramanian, R., N. Otsuka, J. Qiu, L.A. Kolodziejski and R.L. Gunshor, Incorporation processes in MBE growth of ZnSe 95 (1989) 533
Voos, M., Recent developments in optical processes in quantum wells and superlattices: many body effects and field-induced localization 95 (1989) 328
Vvedensky, D.D., see Clarke 95 (1989) 28

Wada, O., H. Nobuhara, M. Makiuchi, H. Hamaguchi, S. Sasa and T. Fujii, AlInAs/GaInAs HEMT application for high performance OEIC receivers 95 (1989) 378
Wagner, B.K., see Benson 95 (1989) 543
Waho, T., F. Yanagawa and Y. Yamada, Initial stage of CaF_2 heteroepitaxy on GaAS(001) substrates 95 (1989) 415
Wakefield, B., see Andrews 95 (1989) 167
Wakita, K., see Kawamura 95 (1989) 349
Walter, W., see Meier 95 (1989) 66
Wang, K.L., see Chang 95 (1989) 451
Watanabe, Y., see Koshiba 95 (1989) 51
Wegschneider, W., see Abstreiter 95 (1989) 431
Weichman, F.L., see Teo 95 (1989) 486
Weimann, G., see Leier 95 (1989) 277
Werner, K., see Kamp 95 (1989) 154
Weyers, M., see Kamp 95 (1989) 154
Whaley, G.J., see Petrich 95 (1989) 23
Whitehouse, C.R., see McConville 95 (1989) 228
Williams, G.M., see McConville 95 (1989) 228
Wong, D., see Li 95 (1989) 296
Wowchak, A.M., see Petrich 95 (1989) 23
Wright, S.L., R.F. Marks, E.D. Marshall, Y.C. Shih and A.B. Young, Growth and characterization of in-situ (In,Ga)As ohmic contacts to n-GaAs 95 (1989) 245
Wu, O.K., F.A. Shirland, J.P. Baukus, J.N. Schulman, G.S. Kamath and E.A. Patten, MBE growth and characterization of Hg-based superlattices 95 (1989) 594

Xu, J.-Z., see Andersson 95 (1989) 215
Xu, Z.-Y., see Andersson 95 (1989) 215

Yacobi, B.G., S. Zemon, C. Jagannath and P. Sheldon, Stress relief in patterned GaAs grown on mismatched substrates 95 (1989) 240
Yamada, H., see Ueda 95 (1989) 38

Yamada, T., E. Tokumitsu, K. Saito, T. Akatsuka, M. Miyauchi, M. Konagai and K. Takahashi, Heavily carbon doped p-type GaAs and GaAlAs grown by metal-organic molecular beam epitaxy 95 (1989) 145
Yamada, Y., see Waho 95 (1989) 415
Yamaga, S., see Yoshikawa 95 (1989) 572
Yamamoto, K., see Iijima 95 (1989) 505
Yamamoto, K., see Terashima 95 (1989) 617
Yamamoto, S., see Takahashi 95 (1989) 333
Yamamoto, S., see Hayakawa 95 (1989) 343
Yamanishi, M., see Kunitsugu 95 (1989) 91
Yanagawa, F., see Waho 95 (1989) 415
Yao, T., H. Nakao, H. Kawanami and R. Toba, Lattice strain relaxation at the initial stages of heteroepitaxy of GaAs on (100)Si by molecular beam epitaxy 95 (1989) 107
Yokoyama, S., J. Oogi, D. Yui and M. Kawabe, Low-temperature selective growth of GaAs by alternately supplying molecular beam epitaxy 95 (1989) 32
Yoneda, K., see Ogata 95 (1989) 500
Yonezu, H., see Tsuji 95 (1989) 405
Yoshida, S., see Miki 95 (1989) 444
Yoshikawa, A., H. Oniyama, S. Yamaga and H. Kasai, A study of growth mechanism of ZnS and ZnSe in MOMBE using dimethylzinc and chalcogen hydrides as reactants 95 (1989) 572
Yoshinobu, T., see Fuyuki 95 (1989) 461
Young, A.B., see Wright 95 (1989) 245
Yui, D., see Yokoyama 95 (1989) 32
Yuri, M., see Ozasa 95 (1989) 171

Zachai, R., see Abstreiter 95 (1989) 431
Zemon, S., see Yacobi 95 (1989) 240
Zhao, J.H., see Li 95 (1989) 296
Zhu, Z., T. Nomura, M. Miyao and M. Hagino, MBE growth mechanisms of ZnSe: flux ratio and substrate temperature 95 (1989) 529
Zogg, H., C. Maissen, J. Masek and S. Blunier, Epitaxial lead chalcogenides on fluoride covered silicon substrates: properties and infrared device fabrication 95 (1989) 562

Journal of Crystal Growth 95 (1989) 635–637
North-Holland, Amsterdam

SUBJECT INDEX

Adsorption 17, 23, 32, 64, 66, 71, 269, 305, 543
Alloys 40
Aluminum
– arsenide 75, 202, 357, 367, 394, 425
– gallium arsenide 17, 66, 87, 150, 206, 247, 253, 266, 273, 281, 292, 305, 309, 317, 328, 357, 382, 386, 390
– gallium indium phosphide 343
– indium arsenide 201, 378
– indium phosphide 163, 333
– organic 145, 150
– oxide 494
Apparatus
– for thin film growth
– – by metalorganic chemical vapor deposition
– – – of III–V compounds 121
– – by metalorganic molecular beam epitaxy
– – – of III–V compounds 121
– – – laser assisted
– – – – of alumina 494
– – by molecular beam epitaxy
– – – of dysprosium barium cuprate 607
– – – of III–V compounds 121
– – – of transition metal dichalcogenides 603
– – – of yttrium barium cuprate 617
– – – for mass production
– – – – of aluminum gallium arsenide 317
– – – – of gallium arsenide 317
– for miscellaneous purposes
– – monitoring flux, in MBE, by cold cathode discharge induced photoemission spectroscopy 621

Cadmium
– manganese telluride 557
– mercury telluride 552, 594
– telluride 543, 552, 557, 564, 567, 584
– zinc telluride 584
Calcium
– fluoride 403, 415
– strontium fluoride 140
Characterization methods
– by absorption spectroscopy 363
– by Auger electron spectroscopy 32, 35, 103, 121, 154, 181, 228, 410, 431, 464, 500, 543, 617
– by cathodoluminescence 66, 96, 167, 240
– by deep level transient spectroscopy 185, 296, 305, 317
– by electrical methods 60, 79, 121, 142, 145, 150, 176, 181, 185, 189, 215, 228, 235, 245, 247, 250, 253, 266, 281, 296, 305, 309, 317, 322, 328, 338, 343, 349, 352, 357, 363, 371, 378, 382, 386, 390, 394, 421, 425, 427, 480, 484, 486, 490, 500, 509, 512, 517, 522, 557, 562, 567, 580, 607, 617
– by electron diffraction 38
– by electron microscopy 38, 43, 66, 87, 96, 113, 154, 158, 167, 193, 210, 224, 228, 240, 260, 281, 309, 338, 375, 382, 398, 410, 425, 427, 431, 447, 455, 468, 476, 490, 494, 500, 538, 552, 580, 584, 594, 607, 617
– by electron probe microanalysis 500
– by emission 375, 621
– by low energy electron diffraction 439, 617
– by magnetic properties 394, 410, 480, 617
– by optical microscopy, 171, 220, 238, 333, 343, 572
– by optical properties 431, 594, 604
– by photoluminescence 66, 158, 163, 176, 185, 193, 202, 206, 210, 215, 260, 273, 277, 281, 292, 305, 328, 333, 338, 343, 375, 382, 509, 512, 517, 525, 538, 557, 580, 589, 594, 599
– by Raman spectroscopy 75, 431, 439, 444, 447, 451
– by reflection high energy electron diffraction 17, 23, 28, 32, 35, 51, 71, 87, 91, 103, 107, 113, 117, 121, 136, 158, 163, 171, 176, 193, 197, 206, 215, 220, 224, 228, 269, 292, 309, 322, 367, 404, 410, 415, 421, 425, 439, 444, 461, 464, 468, 472, 476, 490, 494, 505, 517, 529, 533, 538, 543, 547, 564, 584, 599, 603, 607, 617
– by reflectivity 79
– by Rutherford back scattering 113, 140, 403, 427, 455, 464, 484, 584
– by secondary ion mass spectrometry 150, 154, 257, 301, 322, 382, 405, 421, 480, 484, 500, 512, 517, 584
– by synchrotron radiation 415
– by transmission spectroscopy 235, 562, 567
– by ultraviolet photoemission spectroscopy 427
– by X-ray photoemission spectroscopy 35, 113, 132, 367, 421, 464
– by X-ray techniques 51, 145, 202, 220, 224, 288, 405, 410, 427, 444, 447, 500, 505, 517, 525, 547, 552, 557, 564, 580, 584, 594, 607, 617
Chromium 410
Cobalt
– disilicide 455
Computer simulation 23, 55, 533
Convection 23

Devices 1, 66, 79, 96, 121, 142, 167, 189, 206, 210, 309, 317, 343, 349, 352, 357, 360, 363, 378, 382, 386, 390, 394, 480, 490, 562, 567, 594
Diffusional control 66, 71, 257, 277, 301, 599
Dislocations 79, 87, 96, 107, 193, 210, 220, 228, 245, 281, 431, 455
Dopants 142, 145,181, 247, 253, 257, 292, 296, 301, 317, 343, 378, 382, 421, 476, 480, 484, 512, 517, 543, 589
Dysprosium
– barium cuprate 607

Etching
- chemical 66, 117, 142, 154, 158, 322, 338, 405, 533, 547, 564
- hydrogen plasma 91
- reactive ion 266
- thermal 309, 564

Gallium
- aluminum arsenide 35, 142, 145, 260, 288, 352
- antimonide 235
- arsenide 17, 32, 55, 60, 71, 79, 87, 91, 103, 107, 113, 136, 140, 142, 145, 185, 197, 202, 220, 240, 247, 250, 260, 266, 269, 273, 277, 281, 296, 301, 309, 317, 322, 328, 352, 367, 382, 386, 394, 398, 403, 405, 410, 415, 425, 567
- arsenide antimonide 43, 132, 150, 163, 220, 257, 363
- indium arsenide 121, 145, 150, 154, 378
- indium arsenide phosphide 121, 375
- indium phosphide 333
- organic 91, 121, 132, 136, 140, 150, 154, 158, 167, 171, 181

Germanium 421, 431, 439, 444, 447, 451
Gettering 296

Heterojunction 51, 75, 79, 87, 96, 107, 121, 163, 167, 189, 210, 220, 224, 245, 247, 250, 257, 273, 338, 343, 363, 367, 371, 375, 378, 383, 390, 394, 403, 425, 439, 447, 464, 490, 494, 517, 567

Impurity 154, 281, 301, 305, 322, 382, 500
Indium
- aluminum arsenide 35, 38, 338, 349, 371
- aluminum phosphide 171
- antimonide 228, 567
- arsenide 132, 197, 202, 210, 235
- gallium antimonide 158
- gallium arsenide 35, 167, 181, 189, 193, 215, 224, 245, 281, 338, 349, 363, 371, 390
- organic 121, 154, 158, 167, 171, 176, 181
- phosphide 117, 121, 167, 171, 176, 181

Interface 51, 60, 79, 87, 96, 103, 113, 121, 163, 193, 197, 224, 228, 235, 245, 247, 250, 260, 269, 273, 277, 288, 309, 322, 333, 338, 382, 394, 403, 410, 415, 431, 439, 447, 552, 564, 567
Iron 410

Kinetics
- of growth 23, 28, 32, 48, 55, 66, 91, 113, 136, 140, 142, 171, 193, 197, 260, 269, 301, 305, 461, 468, 476, 494, 522, 529, 533, 538, 543, 572
- of interdiffusion 277
- of interface control 193, 260, 273, 439
- of nucleation 142, 260, 269

Lasers 66, 121, 375, 382
Lattice mismatch 96, 107, 121, 154, 163, 202, 206, 215, 220, 228, 240, 281, 288, 343, 363, 403, 405, 415, 427, 505, 525, 552, 562
Lead
- cadmium chalcogenides 599
- chalcogenides 562
- sulphide 599

Magnesium
- aluminate 500

Mathematical model 48, 64, 529
Mercury
- cadmium telluride 552, 594
- telluride 594

Monte Carlo method 23, 28, 51
Morphology of growth 23, 28, 48, 55, 154, 158, 171, 202, 220, 269, 292, 317, 333, 343, 398, 405, 494, 500, 538, 572, 607

Nickel
- aluminum 425
- disilicide 490
- gallium 427
- oxide 505

Nucleation 23, 48, 71, 197, 245, 415

One–three–di-six ($I–III–VI_2$) compounds 360

Perfection of crystals 17, 38, 43, 87, 96, 113, 117, 176, 185, 224, 281, 296, 309, 317, 403, 431, 447, 455, 476, 484, 517, 522, 538, 552, 557
Phase diagrams 38
Phenomenological theory 55, 572
Precursor 572

Quantum wells/size effects 1, 60, 66, 75, 79, 96, 163, 167, 193, 202, 206, 210, 215, 220, 235, 247, 250, 260, 266, 273, 277, 328, 333, 338, 349, 352, 378, 382, 386, 394, 410, 425, 557, 567, 584, 589, 599

Segregation 35, 257
Silicon 431, 439, 444, 447, 451, 468, 472, 476, 480, 484, 486, 500
- carbide 461
- nitride 464

Step 23, 51, 269, 273, 455
Strain 79, 87, 107, 189, 193, 197, 201, 202, 206, 210, 215, 220, 240, 281, 371, 390, 403, 415, 431, 444, 447, 451, 525, 547, 580
Superconductivity 607, 617, 621
- characterization 607, 617
- high T_c 607, 617, 621
- thin films 607, 617, 621

Supercooling, supersaturation 71
Superlattices 1, 51, 75, 87, 96, 121, 202, 206, 220, 260, 288, 328, 357, 386, 394, 410, 431, 444, 447, 451, 486, 505, 547, 557, 564, 567, 580, 584, 589, 594, 607
Surface processes, theory 23, 71, 305
Surface structure 35, 87, 107, 117, 197, 224, 269, 398, 461, 472, 533, 543

Thermodynamics 201, 529
Thin film growth
- by atomic layer epitaxy

– – of zinc chalcogenides 580
– by metalorganic molecular beam epitaxy
– – of alumina 494
– – of gallium aluminum arsenide 142, 145, 150
– – of gallium arsenide 142, 145, 150
– – of gallium indium arsenide 145, 150, 154, 181
– – of indium aluminum phosphide 171
– – of indium gallium antimonide 158
– – of indium gallium phosphide 171
– – of indium phosphide 167, 181
– – of III–V compounds 121
– – of zinc selenide 572
– – of zinc sulphide 572
– by molecular beam epitaxy
– – current state and future challenge 1
– – of aluminum arsenide 75, 357, 367, 425
– – of aluminum gallium arsenide 17, 66, 206, 247, 253, 260, 266, 273, 281, 288, 292, 305, 309, 317, 352, 357, 382, 386, 390
– – of aluminum gallium indum phosphide 343.
– – of aluminum indium arsenide 201
– – of aluminum indium phosphide 163, 333
– – of cadmium manganese telluride 557
– – of cadmium telluride 543, 552, 557, 564, 567, 584
– – of cadmium zinc telluride 584
– – of calcium fluoride 415
– – of chromium 410
– – of cobalt disilicide 455
– – of dysprosium barium cuprate 607
– – of gallium antimonide 235
– – of gallium arsenide 17, 32, 51, 60, 71, 79, 87, 91, 96, 103, 107, 113, 117, 132, 136, 140, 163, 185, 197, 220, 240, 247, 250, 257, 260, 266, 269, 273, 277, 281, 296, 301, 309, 317, 322, 352, 367, 382, 386, 398, 403, 405, 410, 415, 425
– – of gallium arsenide antimonide 43, 220, 363
– – of gallium indium arsenide phosphide 375
– – of gallium indium phosphide 333
– – of germanium 421, 431, 439, 444, 447, 451
– – of indium aluminum arsenide 38, 338, 349, 371, 378
– – of indium antimonide 228
– – of indium arsenide 132, 197, 210, 235
– – of indium gallium arsenide 189, 193, 215, 224, 245, 281, 338, 349, 363, 371, 378, 390
– – of indium phosphide 176
– – of iron 410
– – of lead cadmium chalcogenides 599
– – of lead chalcogenides 562
– – of lead sulphide 599
– – of mercury cadmium telluride 552, 594
– – of mercury telluride 594
– – of nickel–aluminum 425
– – of nickel disilicide 490
– – of nickel–gallium 427
– – of nickel oxide 505
– – of silicon 431, 439, 444, 447, 451, 468, 472, 476, 480, 484, 486, 500
– – of silicon carbide 461
– – of silicon nitride 464
– – of III–V compounds 11, 35, 121, 202
– – of tin 564
– – of transition metal dichalcogenides 603
– – of yttrium barium cuprate 617
– – of zinc oxide 505
– – of zinc selenide 512, 522, 529, 533, 538, 567, 589
– – of zinc sulphide 505
– – of zinc sulphoselenide 525
– – of zinc telluride 517, 589
– – of zinc tellurosulphide 547
– – theory of 1, 11, 23, 28, 48, 55, 64
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of magnesium aluminate 500
– – through metalorganic chemical vapor deposition
– – – combined with molecular beam epitaxy
– – – – of semiconductors 360
– – – – of III–V compounds 121
– – – theory of 55
Three–five (III–V) compounds 11, 35, 121, 360, 567
Three–five/two–six (III–V/II–VI) heterointerfaces 567
Tin 564
– organic 181
Transition metal
– dichalcogenides 603
Twinning 552
Two–six (II–VI) compounds 360, 567

Yttrium
–barium cuprate 617

Zinc
– oxide 505
– selenide 512, 522, 529, 533, 538, 567, 572, 580, 589
– sulphide 505, 572
– sulphoselenide 525
– telluride 517, 580, 589
– tellurosulphide 547